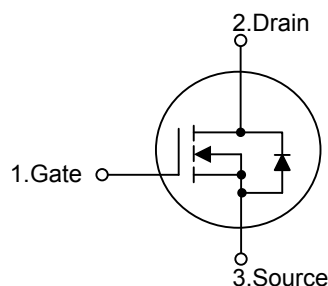


**9NM70-S****Power MOSFET****9A, 700V N-CHANNEL
SUPER-JUNCTION MOSFET****DESCRIPTION**

The UTC 9NM70-S is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

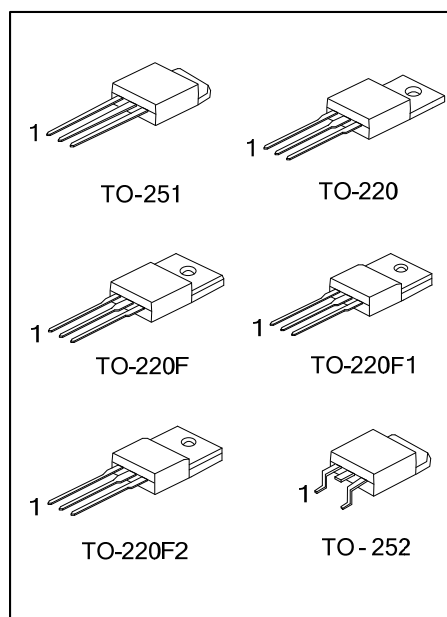
- * $R_{DS(ON)} \leq 0.65 \Omega$ @ $V_{GS}=10V$, $I_D=1.5A$
- * High switching Speed
- * 100% avalanche tested
- * Improved dv/dt capability

SYMBOL**ORDERING INFORMATION**

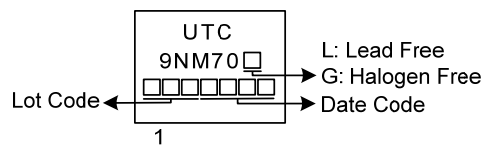
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
9NM70L-TA3-T	9NM70G-TA3-T	TO-220	G	D	S	Tube
9NM70L-TF1-T	9NM70G-TF1-T	TO-220F1	G	D	S	Tube
9NM70L-TF2-T	9NM70G-TF2-T	TO-220F2	G	D	S	Tube
9NM70L-TF3-T	9NM70G-TF3-T	TO-220F	G	D	S	Tube
9NM70L-TM3-T	9NM70G-TM3-T	TO-251	G	D	S	Tube
9NM70L-TN3-R	9NM70G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

9NM70G-TA3-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TM3: TO-251, TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	9	A
	Pulsed (Note 2)	I_{DM}	36	A
Avalanche Current		I_{AR}	2.2	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	242	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.55	V/ns
Power Dissipation	TO-220	P_D	79	W
	TO-220F/TO-220F1		30	W
	TO-220F2		57	W
	TO-251/TO-252		57	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=100\text{mH}$, $I_{AS}=2.2\text{A}$, $V_{DD}=50\text{V}$, $R_G=0\ \Omega$, Starting $T_J=25^\circ\text{C}$

4. $I_{SD} \leq 9.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2		110	
	TO-251/TO-252		110	
Junction to Case	TO-220	θ_{JC}	1.58	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		4.17	
	TO-220F2		4.17	
	TO-251/TO-252		2.19 (Note)	

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

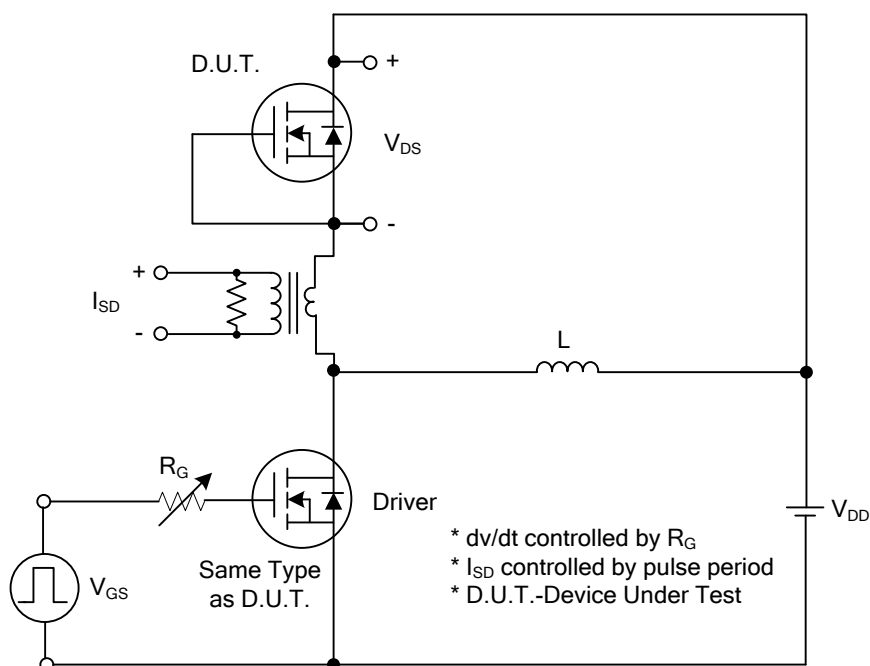
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =1mA, V _{GS} =0V	700			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =700V, V _{GS} =0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V			+100	nA
	Reverse		V _{GS} =-30V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =1.5A			0.65	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		560		pF
Output Capacitance		C _{OSS}			350		pF
Reverse Transfer Capacitance		C _{RSS}			35		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =560V, V _{GS} =10V, I _D =9A , I _G =1mA (Note 1, 2)		21	28	nC
Gate to Source Charge		Q _{GS}			4		nC
Gate to Drain Charge		Q _{GD}			7		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =9A, R _G =25Ω (Note 1, 2)		9		ns
Rise Time		t _R			20		ns
Turn-OFF Delay Time		t _{D(OFF)}			60		ns
Fall-Time		t _F			45		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				9	A
Maximum Body-Diode Pulsed Current		I _{SM}				36	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =9.0A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	I _S =9.0A, V _{GS} =0V,		340		ns
Body Diode Reverse Recovery Charge		Q _{rr}	dl _F /dt=100A/μs		4.27		μC

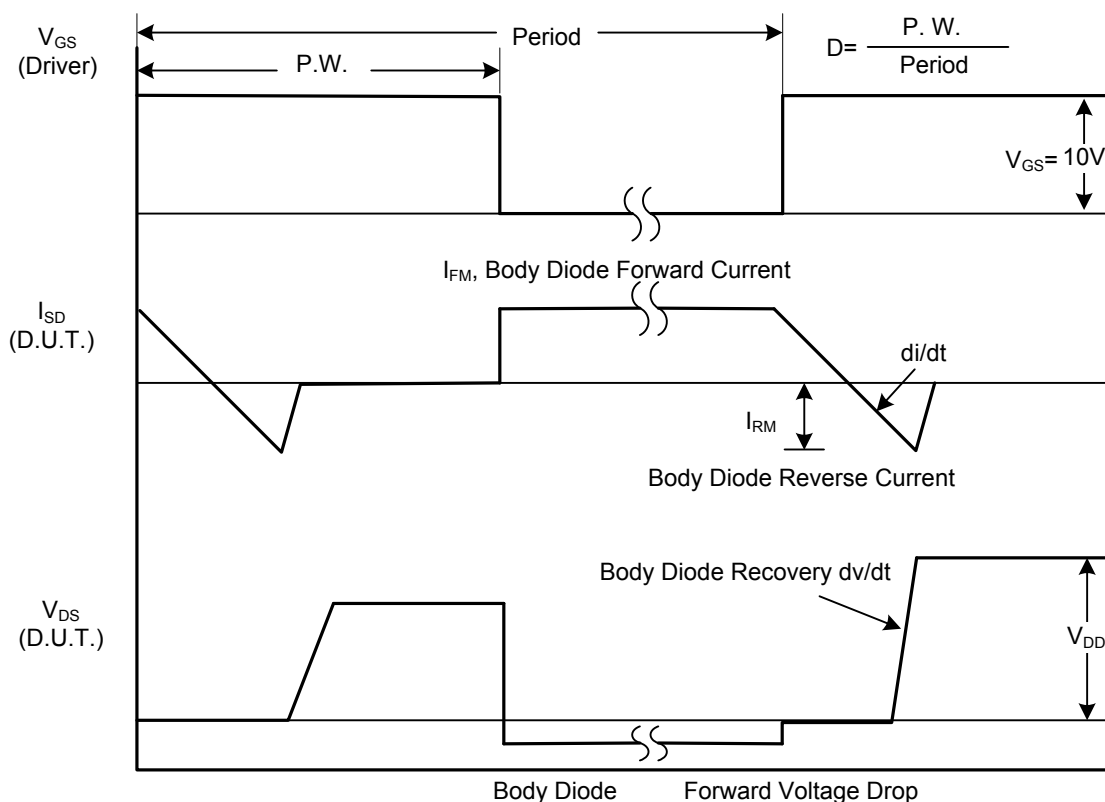
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

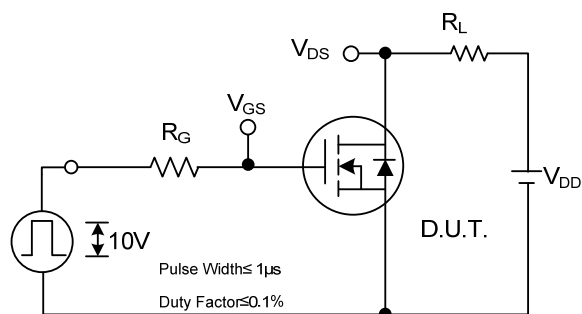


Peak Diode Recovery dv/dt Test Circuit

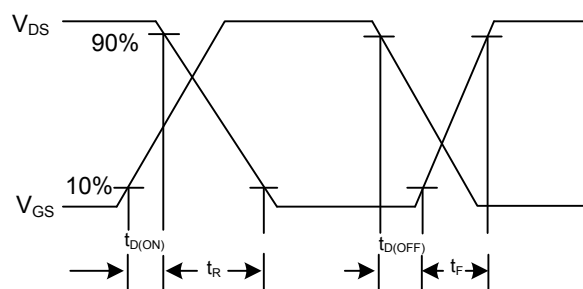


Peak Diode Recovery dv/dt Waveforms

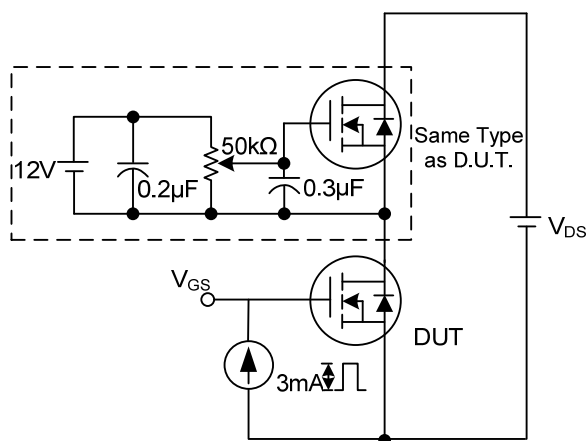
■ TEST CIRCUITS AND WAVEFORMS



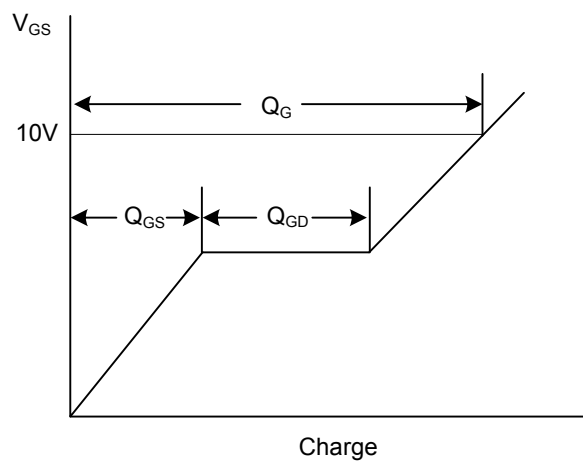
Switching Test Circuit



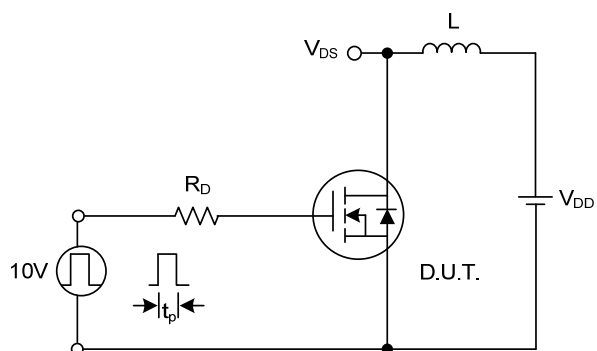
Switching Waveforms



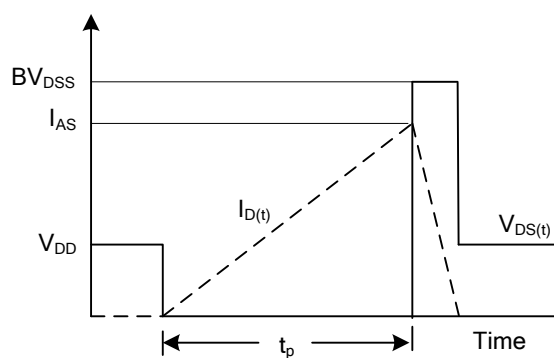
Gate Charge Test Circuit



Gate Charge Waveform

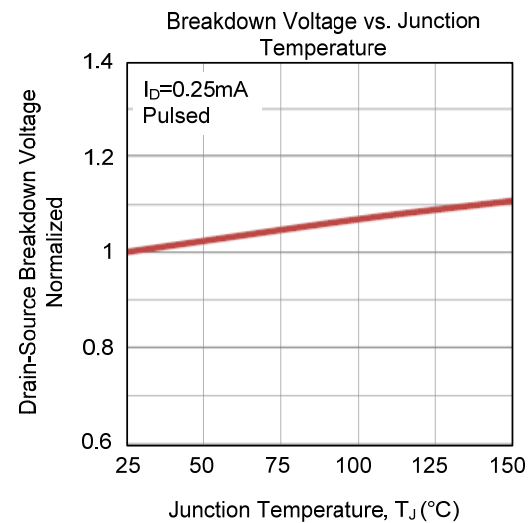
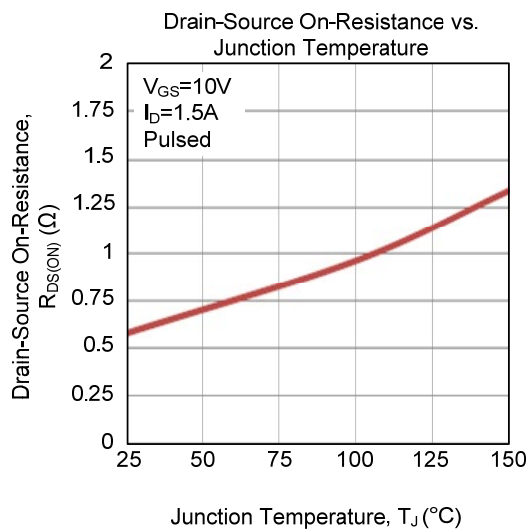
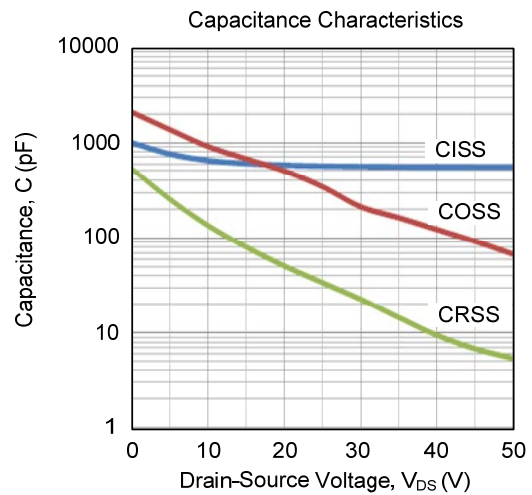
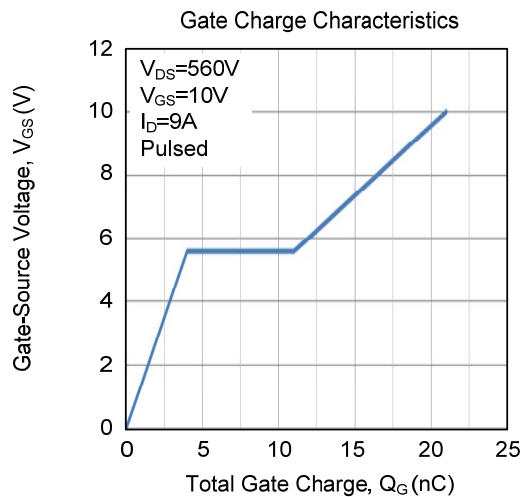
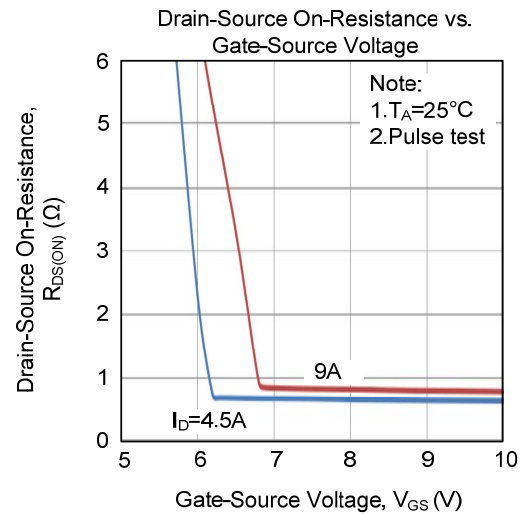
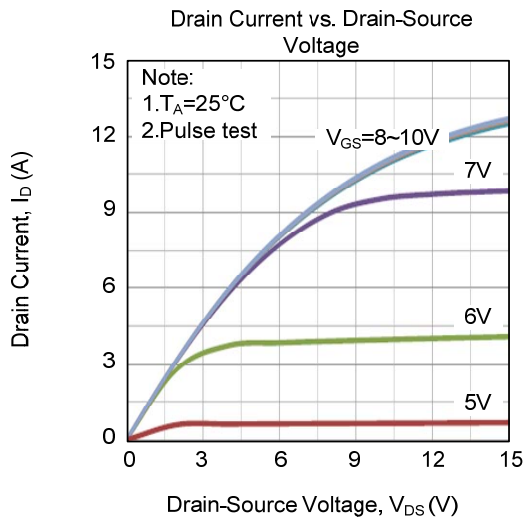


Unclamped Inductive Switching Test Circuit

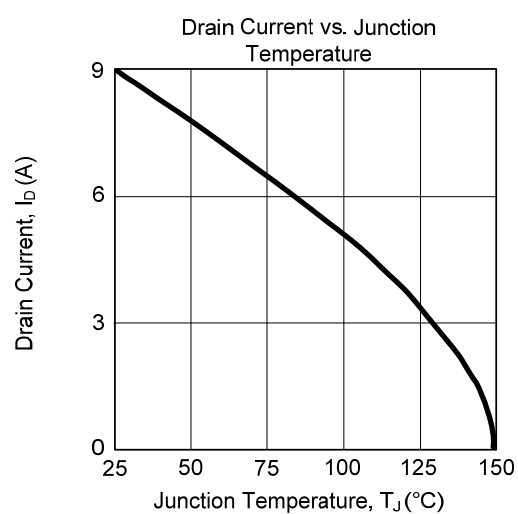
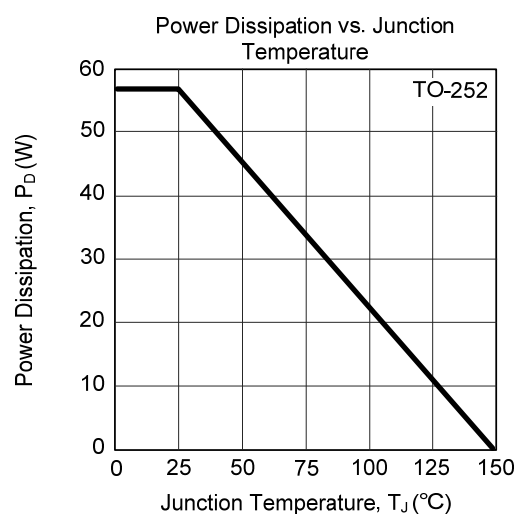
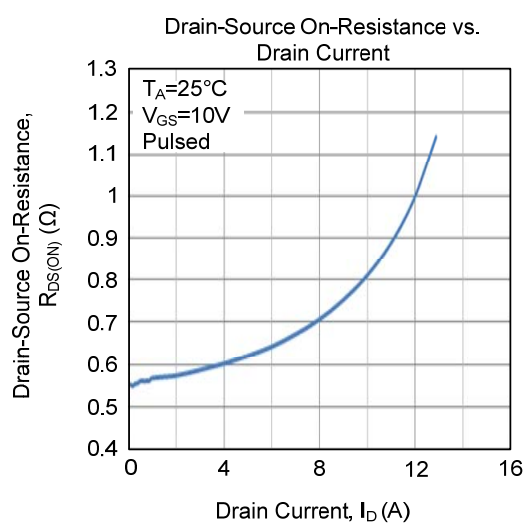
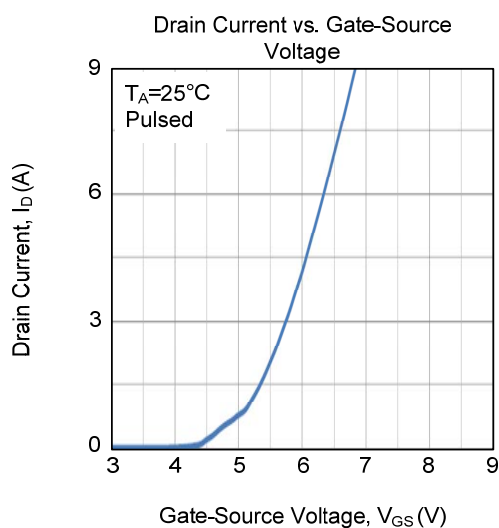
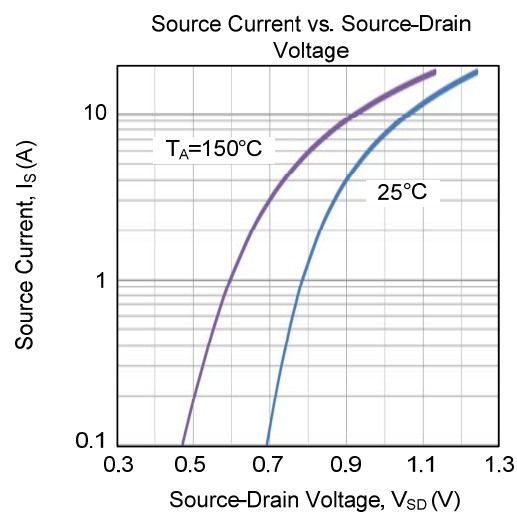
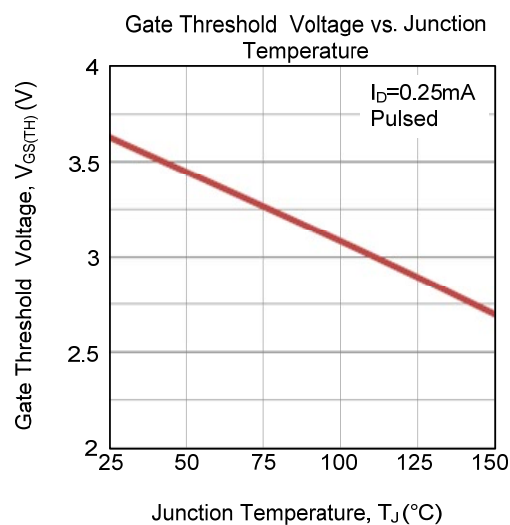


Unclamped Inductive Switching Waveforms

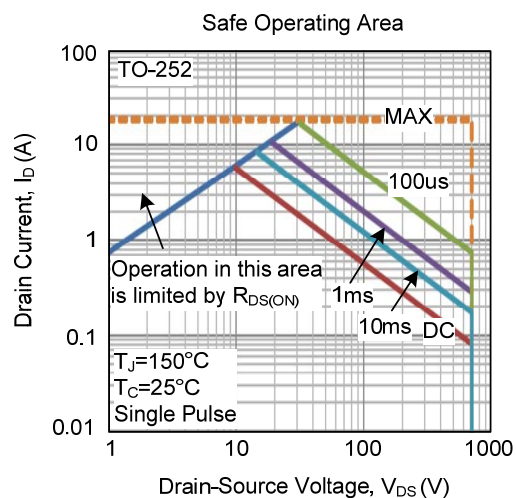
■ TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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